

Radiation Hardened Octal Transparent Latch, Three-State

August 1995

Features

- 3 Micron Radiation Hardened CMOS SOS
- Total Dose 200K RAD (Si)
- SEP Effective LET No Upsets: >100 MEV-cm²/mg
- Single Event Upset (SEU) Immunity < 2 x 10⁻⁹ Errors/Bit-Day (Typ)
- Dose Rate Survivability: >1 x 10¹² RAD (Si)/s
- Dose Rate Upset >10¹⁰ RAD (Si)/s 20ns Pulse
- Latch-Up Free Under Any Conditions
- Fanout (Over Temperature Range)
 - Bus Driver Outputs - 15 LSTTL Loads
- Military Temperature Range: -55°C to +125°C
- Significant Power Reduction Compared to LSTTL ICs
- DC Operating Voltage Range: 4.5V to 5.5V
- LSTTL Input Compatibility
 - VIL = 0.8V Max
 - VIH = VCC/2 Min
- Input Current Levels I_i ≤ 5μA at VOL, VOH

Description

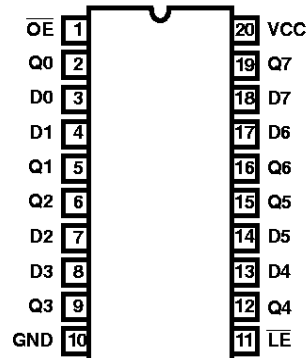
The Harris HCTS373MS is a Radiation Hardened octal transparent three-state latch with an active-low output enable. The outputs are transparent to the inputs when the Latch Enable (\overline{LE}) is HIGH. When the Latch Enable (\overline{LE}) goes LOW, the data is latched. The Output Enable (\overline{OE}) controls the three-state outputs. When the Output Enable (\overline{OE}) is HIGH, the outputs are in the high impedance state. The latch operation is independent of the state of the Output Enable.

The HCTS373MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of radiation hardened, high-speed, CMOS/SOS Logic Family.

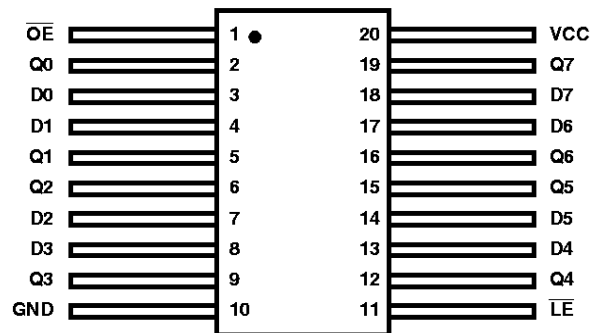
The HCTS373MS is supplied in a 20 lead Ceramic flatpack (K suffix) or a SBDIP Package (D suffix).

Pinouts

20 LEAD CERAMIC DUAL-IN-LINE
METAL SEAL PACKAGE (SBDIP)
MIL-STD-1835 CDIP2-T20
TOP VIEW



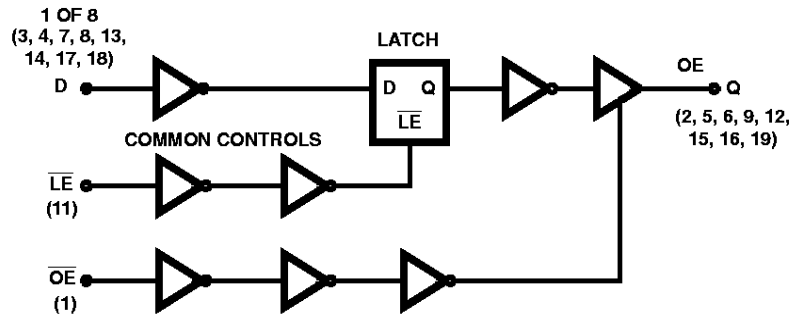
20 LEAD CERAMIC METAL SEAL
FLATPACK PACKAGE (FLATPACK)
MIL-STD-1835 CDFP4-F20
TOP VIEW



Ordering Information

| PART NUMBER | TEMPERATURE RANGE | SCREENING LEVEL | PACKAGE |
|-----------------|-------------------|---------------------------|--------------------------|
| HCTS373DMSR | -55°C to +125°C | Harris Class S Equivalent | 20 Lead SBDIP |
| HCTS373KMSR | -55°C to +125°C | Harris Class S Equivalent | 20 Lead Ceramic Flatpack |
| HCTS373D/Sample | +25°C | Sample | 20 Lead SBDIP |
| HCTS373K/Sample | +25°C | Sample | 20 Lead Ceramic Flatpack |
| HCTS373HMSR | +25°C | Die | Die |

Functional Diagram



TRUTH TABLE

| \overline{OE} | \overline{LE} | D | Q |
|-----------------|-----------------|---|---|
| L | H | H | H |
| L | H | L | L |
| L | L | l | L |
| L | L | h | H |
| H | X | X | Z |

H = High Level, L = Low Level

X = Immaterial, Z = High Impedance

l = Low voltage level prior to the high-to-low latch enable transition

h = High voltage level prior to the high-to-low latch enable transition

Specifications HCTS373MS

Absolute Maximum Ratings

| | |
|---|--------------------|
| Supply Voltage (VCC) | -0.5V to +7.0V |
| Input Voltage Range, All Inputs | -0.5V to VCC +0.5V |
| DC Input Current, Any One Input | ±10mA |
| DC Drain Current, Any One Output (All Voltage Reference to the VSS Terminal) | ±25mA |
| Storage Temperature Range (TSTG) | -65°C to +150°C |
| Lead Temperature (Soldering 10sec) | +265°C |
| Junction Temperature (TJ) | +175°C |
| ESD Classification | Class 1 |

Reliability Information

| | | |
|--|---------------|---------------|
| Thermal Resistance | θ_{JA} | θ_{JC} |
| SBDIP Package | 72°C/W | 24°C/W |
| Ceramic Flatpack Package | 107°C/W | 28°C/W |
| Maximum Package Power Dissipation at +125°C Ambient | | |
| SBDIP Package | | 0.69W |
| Ceramic Flatpack Package | | 0.47W |
| If device power exceeds package dissipation capability, provide heat sinking or derate linearly at the following rate: | | |
| SBDIP Package | | 13.9mW/°C |
| Ceramic Flatpack Package | | 9.3mW/°C |

CAUTION: As with all semiconductors, stress listed under "Absolute Maximum Ratings" may be applied to devices (one at a time) without resulting in permanent damage. This is a stress rating only. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. The conditions listed under "Electrical Performance Characteristics" are the only conditions recommended for satisfactory device operation..

Operating Conditions

| | | | |
|--|-----------------|--------------------------|--------------|
| Supply Voltage (VCC) | +4.5V to +5.5V | Input Low Voltage (VIL) | 0.0V to 0.8V |
| Input Rise and Fall Times at VCC = 4.5V (TR, TF) | .500ns Max | Input High Voltage (VIH) | VCC/2 to VCC |
| Operating Temperature Range (TA) | -55°C to +125°C | | |

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

| PARAMETER | SYMBOL | (NOTE 1) CONDITIONS | GROUP A SUB- GROUPS | TEMPERATURE | LIMITS | | UNITS |
|-----------------------------------|--------|---|---------------------------|----------------------|-------------|------|-------|
| | | | | | MIN | MAX | |
| Quiescent Current | ICC | VCC = 5.5V, VIN = VCC or GND | 1 | +25°C | - | 40 | μA |
| | | | 2, 3 | +125°C, -55°C | - | 750 | μA |
| Output Current (Sink) | IOL | VCC = 4.5V, VIH = 4.5V, VOUT = 0.4V, VIL = 0V | 1 | +25°C | 7.2 | - | mA |
| | | | 2, 3 | +125°C, -55°C | 6.0 | - | mA |
| Output Current (Source) | IOH | VCC = 4.5V, VIH = 4.5V, VOUT = VCC - 0.4V, VIL = 0V | 1 | +25°C | -7.2 | - | mA |
| | | | 2, 3 | +125°C, -55°C | -6.0 | - | mA |
| Output Voltage Low | VOL | VCC = 4.5V, VIH = 2.25V, IOL = 50μA, VIL = 0.8V | 1, 2, 3 | +25°C, +125°C, -55°C | - | 0.1 | V |
| | | VCC = 5.5V, VIH = 2.75V, IOL = 50μA, VIL = 0.8V | 1, 2, 3 | +25°C, +125°C, -55°C | - | 0.1 | V |
| Output Voltage High | VOH | VCC = 4.5V, VIH = 2.25V, IOH = -50μA, VIL = 0.8V | 1, 2, 3 | +25°C, +125°C, -55°C | VCC -0.1 | - | V |
| | | VCC = 5.5V, VIH = 2.75V, IOH = -50μA, VIL = 0.8V | 1, 2, 3 | +25°C, +125°C, -55°C | VCC -0.1 | - | V |
| Input Leakage Current | IIN | VCC = 5.5V, VIN = VCC or GND | 1 | +25°C | - | ±0.5 | μA |
| | | | 2, 3 | +125°C, -55°C | - | ±5.0 | μA |
| Output Tri State Leakage | IOZ | VCC = 5.5V, VO = 0V or VCC | 1 | +25°C | - | ±1.0 | μA |
| | | | 2, 3 | +125°C, -55°C | | ±50 | μA |
| Noise Immunity Functional Test | FN | VCC = 4.5V, VIH = 2.25V, VIL = 0.8V (Note 2) | 7, 8A, 8B | +25°C, +125°C, -55°C | - | - | - |

NOTES:

1. All voltages reference to device GND.
2. For functional tests VO ≥ 4.0V is recognized as a logic "1", and VO ≤ 0.5V is recognized as a logic "0".

Specifications HCTS373MS

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

| PARAMETER | SYMBOL | (NOTES 1, 2) CONDITIONS | GROUP A SUB- GROUPS | TEMPERATURE | LIMITS | | UNITS |
|-------------------|---------------|----------------------------|---------------------------|---------------|--------|-----|-------|
| | | | | | MIN | MAX | |
| Data to Qn | TPLH | VCC = 4.5V | 9 | +25°C | 2 | 19 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 24 | ns |
| | TPHL | VCC = 4.5V | 9 | +25°C | 2 | 26 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 30 | ns |
| LE to Qn | TPLH | VCC = 4.5V | 9 | +25°C | 2 | 27 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 30 | ns |
| | TPHL | VCC = 4.5V | 9 | +25°C | 2 | 30 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 34 | ns |
| Enable to Output | TPZL | VCC = 4.5V | 9 | +25°C | 2 | 32 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 36 | ns |
| | TPZH | VCC = 4.5V | 9 | +25°C | 2 | 26 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 29 | ns |
| Disable to Output | TPLZ, TPHZ | VCC = 4.5V | 9 | +25°C | 2 | 22 | ns |
| | | | 10, 11 | +125°C, -55°C | 2 | 25 | ns |

NOTES:

1. All voltages referenced to device GND.
2. AC measurements assume RL = 500Ω, CL = 50pF, Input TR = TF = 3ns, VIL = GND, VIH = 3V.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | LIMITS | | UNITS |
|----------------------------------|--------------|----------------------|-------|---------------|--------|-----|-------|
| | | | | | MIN | MAX | |
| Capacitance Power Dissipation | CPD | VCC = 5.0V, f = 1MHz | 1 | +25°C | - | 57 | pF |
| | | | 1 | +125°C, -55°C | - | 57 | pF |
| Input Capacitance | CIN | VCC = 5.0V, f = 1MHz | 1 | +25°C | - | 10 | pF |
| | | | 1 | +125°C, -55°C | - | 10 | pF |
| Output Transition Time | TTHL TTLH | VCC = 4.5V | 1 | +25°C | - | 12 | ns |
| | | | 1 | +125°C, -55°C | - | 18 | ns |
| Setup Time Data to LE | TSU | VCC = 4.5V | 1 | +25°C | 13 | - | ns |
| | | | 1 | +125°C, -55°C | 20 | - | ns |
| Hold Time Data to LE | TH | VCC = 4.5V | 1 | +25°C | 10 | - | ns |
| | | | 1 | +125°C, -55°C | 15 | - | ns |
| Pulse Width LE | TW | VCC = 4.5V | 1 | +25°C | 16 | - | ns |
| | | | 1 | +125°C, -55°C | 24 | - | ns |

NOTE:

1. The parameters listed in Table 3 are controlled via design or process parameters. Min and Max Limits are guaranteed but not directly tested. These parameters are characterized upon initial design release and upon design changes which affect these characteristics.

Specifications HCTS373MS

TABLE 4. DC POST RADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

| PARAMETER | SYMBOL | (NOTES 1, 2) CONDITIONS | TEMPERATURE | 200K RAD LIMITS | | UNITS |
|------------------------------------|------------|---|-------------|-----------------|------|-------|
| | | | | MIN | MAX | |
| Quiescent Current | ICC | VCC = 5.5V, VIN = VCC or GND | +25°C | - | 0.75 | mA |
| Output Current (Sink) | IOL | VCC = 4.5V, VIN = VCC or GND, VOUT = 0.4V | +25°C | 6.0 | - | mA |
| Output Current (Source) | IOH | VCC = 4.5V, VIN = VCC or GND, VOUT = VCC - 0.4V | +25°C | -6.0 | - | mA |
| Output Voltage Low | VOL | VCC = 4.5V and 5.5V, VIH = VCC/2, VIL = 0.8V, IOL = 50μA | +25°C | - | 0.1 | V |
| Output Voltage High | VOH | VCC = 4.5V and 5.5V, VIH = VCC/2, VIL = 0.8V, IOH = -50μA | +25°C | VCC - 0.1 | - | V |
| Input Leakage Current | IIN | VCC = 5.5V, VIN = VCC or GND | +25°C | - | ±5 | μA |
| Three-State Output Leakage Current | IOZ | Applied Voltage = 0V or VCC, VCC = 5.5V | +25°C | - | ±50 | μA |
| Noise Immunity Functional Test | FN | VCC = 4.5V, VIH = 2.25V, VIL = 0.8V, (Note 3) | +25°C | - | - | - |
| Data to Qn | TPLH | VCC = 4.5V | +25°C | 2 | 24 | ns |
| | TPHL | VCC = 4.5V | +25°C | 2 | 30 | ns |
| LE to Qn | TPLH | VCC = 4.5V | +25°C | 2 | 30 | ns |
| | TPHL | VCC = 4.5V | +25°C | 2 | 34 | ns |
| Enable to Output | TPZL | VCC = 4.5V | +25°C | 2 | 36 | ns |
| | TPZH | VCC = 4.5V | +25°C | 2 | 29 | ns |
| Disable to Output | TPLZ, TPHZ | VCC = 4.5V | +25°C | 2 | 25 | ns |

NOTES:

1. All voltages referenced to device GND.
2. AC measurements assume RL = 500Ω, CL = 50pF, Input TR = TF = 3ns, VIL = GND, VIH = 3V.
3. For functional tests VO ≥ 4.0V is recognized as a logic "1", and VO ≤ 0.5V is recognized as a logic "0".

TABLE 5. BURN-IN AND OPERATING LIFE TEST, DELTA PARAMETERS (+25°C)

| PARAMETER | GROUP B SUBGROUP | DELTA LIMIT |
|-----------|------------------|----------------|
| ICC | 5 | 12μA |
| IOL/IOH | 5 | -15% of 0 Hour |
| IOZL/IOZH | 5 | ±200nA |

Specifications HCTS373MS

TABLE 6. APPLICABLE SUBGROUPS

| CONFORMANCE GROUPS | | METHOD | GROUP A SUBGROUPS | READ AND RECORD |
|--------------------------------|--------------|-------------|---------------------------------------|------------------------------|
| Initial Test (Preburn-In) | | 100%/5004 | 1, 7, 9 | ICC, IOL/H |
| Interim Test I (Postburn-In) | | 100%/5004 | 1, 7, 9 | ICC, IOL/H |
| Interim Test II (Postburn-In) | | 100%/5004 | 1, 7, 9 | ICC, IOL/H |
| PDA | | 100%/5004 | 1, 7, 9, Deltas | |
| Interim Test III (Postburn-In) | | 100%/5004 | 1, 7, 9 | ICC, IOL/H |
| PDA | | 100%/5004 | 1, 7, 9, Deltas | |
| Final Test | | 100%/5004 | 2, 3, 8A, 8B, 10, 11 | |
| Group A (Note 1) | | Sample/5005 | 1, 2, 3, 7, 8A, 8B, 9, 10, 11 | |
| Group B | Subgroup B-5 | Sample/5005 | 1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas | Subgroups 1, 2, 3, 9, 10, 11 |
| | Subgroup B-6 | Sample/5005 | 1, 7, 9 | |
| Group D | | Sample/5005 | 1, 7, 9 | |

NOTE:

1. Alternate Group A testing in accordance with method 5005 of MIL-STD-883 may be exercised.

TABLE 7. TOTAL DOSE IRRADIATION

| CONFORMANCE GROUPS | METHOD | TEST | | READ AND RECORD | |
|--------------------|--------|---------|----------|-----------------|------------------|
| | | PRE RAD | POST RAD | PRE RAD | POST RAD |
| Group E Subgroup 2 | 5005 | 1, 7, 9 | Table 4 | 1, 9 | Table 4 (Note 1) |

NOTE:

1. Except FN test which will be performed 100% Go/No-Go.

TABLE 8. STATIC AND DYNAMIC BURN-IN TEST CONNECTIONS

| OPEN | GROUND | 1/2 VCC = 3V ± 0.5V | VCC = 6V ± 0.5V | OSCILLATOR | |
|---|---------------------------------------|----------------------------|---------------------------------------|------------|----------------------------|
| | | | | 50kHz | 25kHz |
| STATIC BURN-IN I TEST CONNECTIONS (Note 1) | | | | | |
| 2, 5, 6, 9, 12, 15, 16, 19 | 1, 3, 4, 7, 8, 10, 11, 13, 14, 17, 18 | - | 20 | - | - |
| STATIC BURN-IN II TEST CONNECTIONS (Note 1) | | | | | |
| 2, 5, 6, 9, 12, 15, 16, 19 | 10 | - | 1, 3, 4, 7, 8, 11, 13, 14, 17, 18, 20 | - | - |
| DYNAMIC BURN-IN TEST CONNECTIONS (Note 2) | | | | | |
| - | 1, 10 | 2, 5, 6, 9, 12, 15, 16, 19 | 20 | 11 | 3, 4, 7, 8, 13, 14, 17, 18 |

NOTES:

1. Each pin except VCC and GND will have a resistor of 10kΩ ± 5% for static burn-in
2. Each pin except VCC and GND will have a resistor of 680Ω ± 5% for dynamic burn-in

TABLE 9. IRRADIATION TEST CONNECTIONS

| OPEN | GROUND | VCC = 5V ± 0.5V |
|----------------------------|--------|---------------------------------------|
| 2, 5, 6, 9, 12, 15, 16, 19 | 10 | 1, 3, 4, 7, 8, 11, 13, 14, 17, 18, 20 |

NOTE: Each pin except VCC and GND will have a resistor of 47kΩ ± 5% for irradiation testing. Group E, Subgroup 2, sample size is 4 dice/wafer 0 failures.

HCTS373MS

Harris Space Level Product Flow - 'MS'

| | |
|--|--|
| Wafer Lot Acceptance (All Lots) Method 5007 (Includes SEM) | 100% Interim Electrical Test 1 (T1) 100% Delta Calculation (T0-T1) |
| GAMMA Radiation Verification (Each Wafer) Method 1019, 4 Samples/Wafer, 0 Rejects | 100% Static Burn-In 2, Condition A or B, 24 hrs. min., +125°C min., Method 1015 |
| 100% Nondestructive Bond Pull, Method 2023 | 100% Interim Electrical Test 2 (T2) |
| Sample - Wire Bond Pull Monitor, Method 2011 | 100% Delta Calculation (T0-T2) |
| Sample - Die Shear Monitor, Method 2019 or 2027 | 100% PDA 1, Method 5004 (Notes 1 and 2) |
| 100% Internal Visual Inspection, Method 2010, Condition A | 100% Dynamic Burn-In, Condition D, 240 hrs., +125°C or Equivalent, Method 1015 |
| 100% Temperature Cycle, Method 1010, Condition C, 10 Cycles | 100% Interim Electrical Test 3 (T3) |
| 100% Constant Acceleration, Method 2001, Condition per Method 5004 | 100% Delta Calculation (T0-T3) |
| 100% PIND, Method 2020, Condition A | 100% PDA 2, Method 5004 (Note 2) |
| 100% External Visual | 100% Final Electrical Test |
| 100% Serialization | 100% Fine/Gross Leak, Method 1014 |
| 100% Initial Electrical Test (T0) | 100% Radiographic, Method 2012 (Note 3) |
| 100% Static Burn-In 1, Condition A or B, 24 hrs. min., +125°C min., Method 1015 | 100% External Visual, Method 2009 Sample - Group A, Method 5005 (Note 4) 100% Data Package Generation (Note 5) |

NOTES:

1. Failures from Interim electrical test 1 and 2 are combined for determining PDA 1.
2. Failures from subgroup 1, 7, 9 and deltas are used for calculating PDA. The maximum allowable PDA = 5% with no more than 3% of the failures from subgroup 7.
3. Radiographic (X-Ray) inspection may be performed at any point after serialization as allowed by Method 5004.
4. Alternate Group A testing may be performed as allowed by MIL-STD-883, Method 5005.
5. Data Package Contents:
 - Cover Sheet (Harris Name and/or Logo, P.O. Number, Customer Part Number, Lot Date Code, Harris Part Number, Lot Number, Quantity).
 - Wafer Lot Acceptance Report (Method 5007). Includes reproductions of SEM photos with percent of step coverage.
 - GAMMA Radiation Report. Contains Cover page, disposition, Rad Dose, Lot Number, Test Package used, Specification Numbers, Test equipment, etc. Radiation Read and Record data on file at Harris.
 - X-Ray report and film. Includes penetrometer measurements.
 - Screening, Electrical, and Group A attributes (Screening attributes begin after package seal).
 - Lot Serial Number Sheet (Good units serial number and lot number).
 - Variables Data (All Delta operations). Data is identified by serial number. Data header includes lot number and date of test.
 - The Certificate of Conformance is a part of the shipping invoice and is not part of the Data Book. The Certificate of Conformance is signed by an authorized Quality Representative.

AC Timing Diagrams

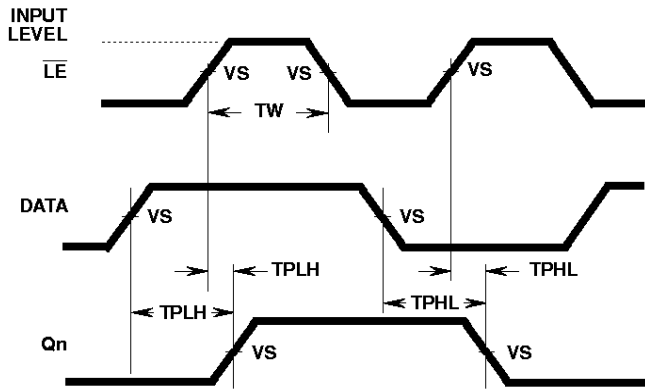


FIGURE 1. DATA AND LATCH ENABLE PROPAGATION DELAYS

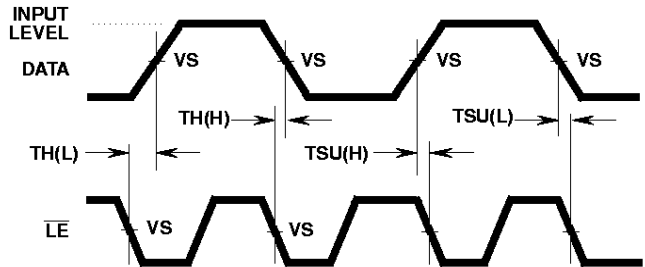


FIGURE 2. LATCH ENABLE PREREQUISITE TIMES

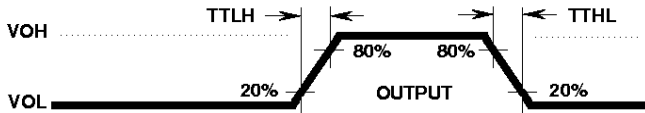
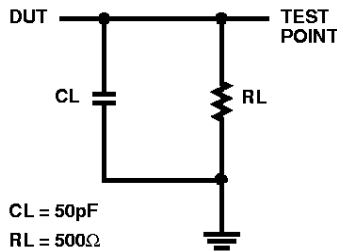


FIGURE 3. DATA SET-UP AND HOLD TIMES

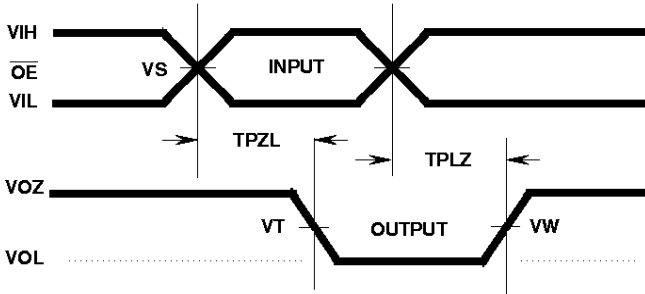
AC VOLTAGE LEVELS

| PARAMETER | HCTS | UNITS |
|-----------|------|-------|
| VCC | 4.50 | V |
| VIH | 3.00 | V |
| VS | 1.30 | V |
| VIL | 0 | V |
| GND | 0 | V |

AC Load Circuit



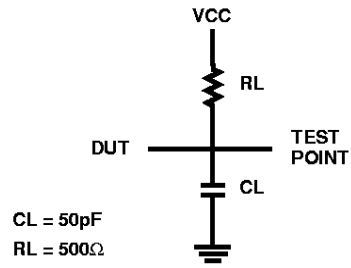
Three-State Low Timing Diagram



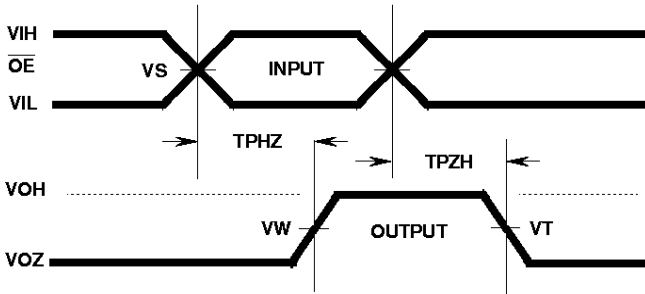
THREE-STATE LOW VOLTAGE LEVELS

| PARAMETER | HCTS | UNITS |
|-----------|------|-------|
| VCC | 4.50 | V |
| VIH | 3.00 | V |
| VS | 1.30 | V |
| VT | 1.30 | V |
| VW | 0.90 | V |
| VIL | 0 | V |
| GND | 0 | V |

Three-State Load Circuit



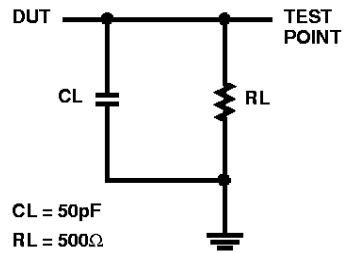
Three-State High Timing Diagram



THREE-STATE HIGH VOLTAGE LEVELS

| PARAMETER | HCTS | UNITS |
|-----------|------|-------|
| VCC | 4.50 | V |
| VIH | 3.00 | V |
| VS | 1.30 | V |
| VT | 1.30 | V |
| VW | 3.60 | V |
| VIL | 0 | V |
| GND | 0 | V |

Three-State Load Circuit



HCTS373MS

Die Characteristics

DIE DIMENSIONS:

108 x 106 mils

METALLIZATION:

Type: SiAl

Metal Thickness: $11\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$

GLASSIVATION:

Type: SiO_2

Thickness: $13\text{k}\text{\AA} \pm 2.6\text{k}\text{\AA}$

WORST CASE CURRENT DENSITY:

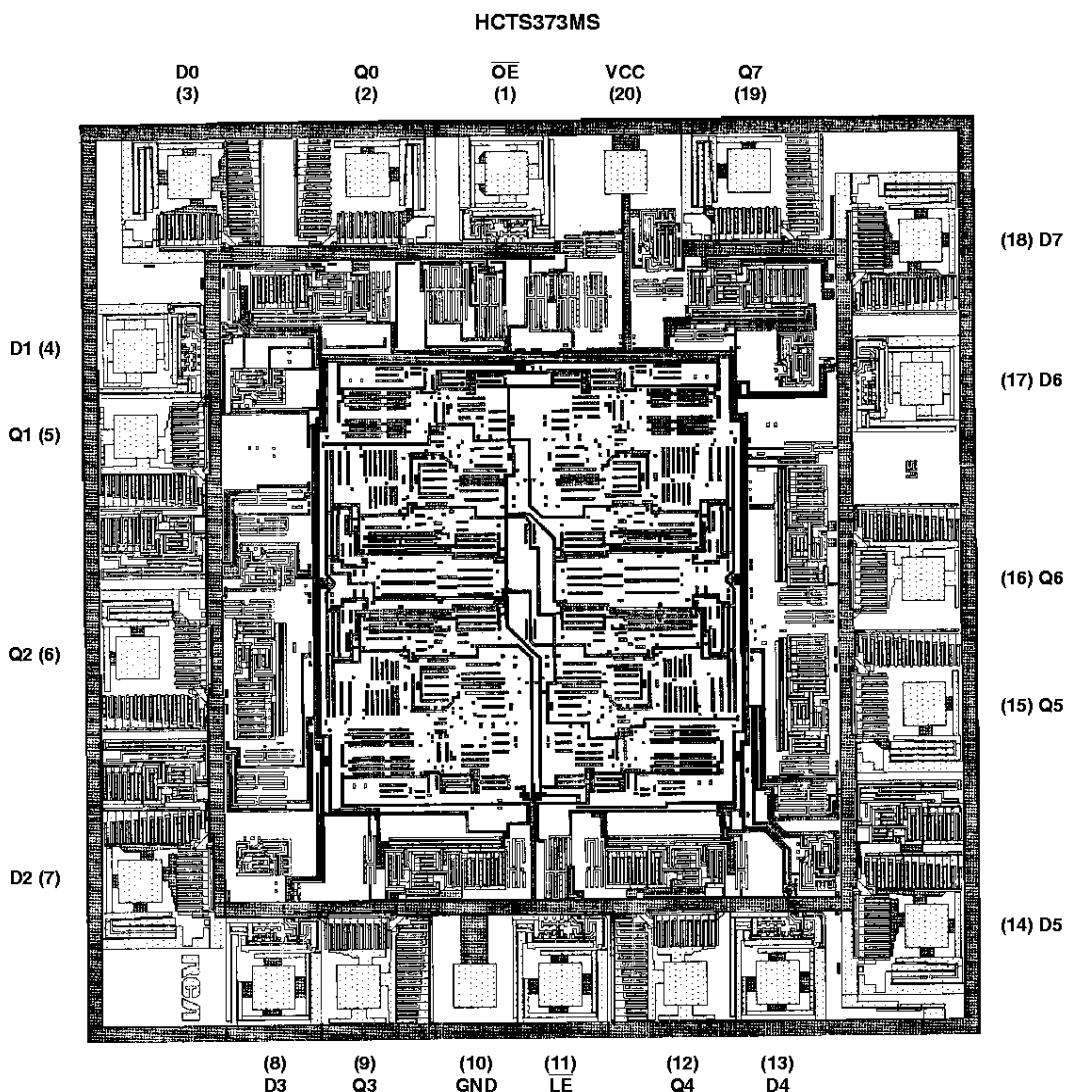
$2.0 \times 10^5 \text{A/cm}^2$

BOND PAD SIZE:

$100\mu\text{m} \times 100\mu\text{m}$

4 x 4 mils

Metallization Mask Layout



NOTE: The die diagram is a generic plot from a similar HCS device. It is intended to indicate approximate die size and bond pad location. The mask series for the HCTS373 is TA14403A.